

**HIGH-SPEED SWITCHING/HIGH ISOLATION VOLTAGE  
PHOTOCOUPLER SERIES**

–NEPOC Series–

**DESCRIPTION**

The PS2513-1 and PS2513L-1 are optically coupled isolators containing a GaAs light emitting diode and an NPN silicon phototransistor.

The PS2513-1 is in a plastic DIP (Dual In-line Package) and the PS2513L-1 is lead bending type (Gull-wing) for surface mount.

**FEATURES**

- High isolation voltage ( $BV = 5\,000\text{ V r.m.s.}$ )
- High collector to emitter voltage ( $V_{CEO} = 120\text{ V}$ )
- Guaranteed maximum switching speed ( $t_{off} \leq 60\text{ }\mu\text{s}$  @  $I_F = 5\text{ mA}$ ,  $V_{CC} = 5\text{ V}$ ,  $R_L = 1.9\text{ k}\Omega$ )
- High-speed switching ( $t_{on} = 5\text{ }\mu\text{s}$  TYP. @  $I_F = 5\text{ mA}$ ,  $V_{CC} = 5\text{ V}$ ,  $R_L = 1.9\text{ k}\Omega$ )  
( $t_{off} = 25\text{ }\mu\text{s}$  TYP. @  $I_F = 5\text{ mA}$ ,  $V_{CC} = 5\text{ V}$ ,  $R_L = 1.9\text{ k}\Omega$ )
- Ordering number of tape product: PS2513L-1-E3, E4, F3, F4

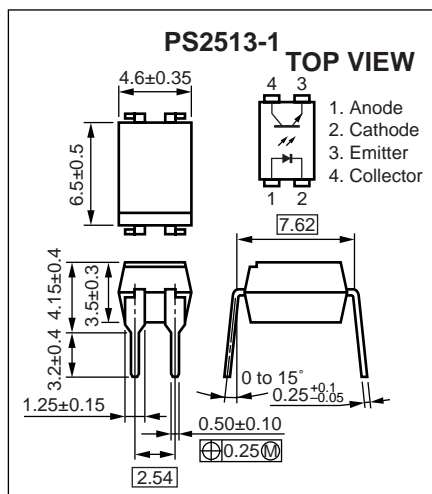
**APPLICATIONS**

- Power supply
- Air conditioner
- FA equipment

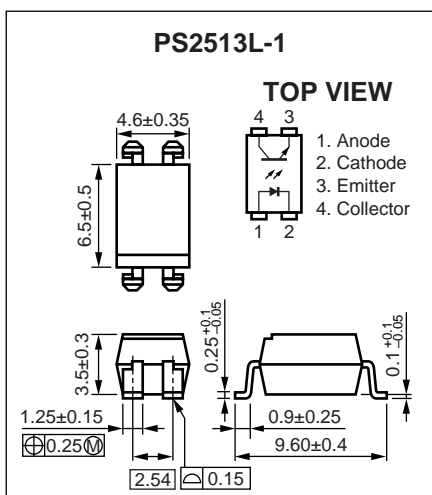
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Not all devices/types available in every country. Please check with local NEC Compound Semiconductor Devices representative for availability and additional information.

PACKAGE DIMENSIONS (UNIT: mm)

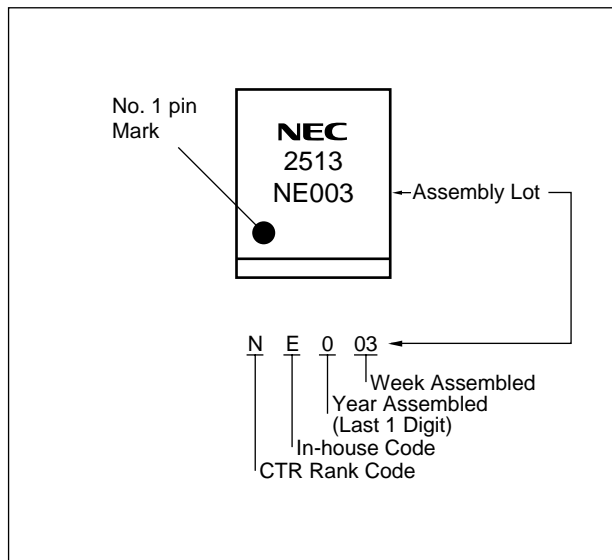
DIP Type



Lead Bneiding Type



# MARKING EXAMPLE



# ORDERING INFORMATION

Part Number	Package	Packing Style	Application Part Number <sup>*1</sup>
PS2513-1	4-pin DIP	Magazine case 100 pcs	PS2513-1
PS2513L-1			
PS2513L-1-E3		Embossed Tape 1 000 pcs/reel	
PS2513L-1-E4			
PS2513L-1-F3		Embossed Tape 2 000 pcs/reel	
PS2513L-1-F4			

<sup>\*1</sup> For the application of the Safety Standard, following part number should be used.

## ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub> = 25°C, unless otherwise specified)

Parameter		Symbol	Ratings	Unit
			PS2513-1, PS2513L-1	
Diode	Reverse Voltage	V <sub>R</sub>	6	V
	Forward Current (DC)	I <sub>F</sub>	60	mA
	Power Dissipation Derating	ΔP <sub>D</sub> /°C	1.5	mW/°C
	Power Dissipation	P <sub>D</sub>	150	mW
	Peak Forward Current <sup>*1</sup>	I <sub>FP</sub>	1	A
Transistor	Collector to Emitter Voltage	V <sub>CEO</sub>	120	V
	Emitter to Collector Voltage	V <sub>ECO</sub>	6	V
	Collector Current	I <sub>C</sub>	30	mA
	Power Dissipation Derating	ΔP <sub>C</sub> /°C	1.5	mW/°C
	Power Dissipation	P <sub>C</sub>	150	mW
Isolation Voltage <sup>*2</sup>		BV	5 000	Vr.m.s.
Operating Ambient Temperature		T <sub>A</sub>	−55 to +100	°C
Storage Temperature		T <sub>stg</sub>	−55 to +150	°C

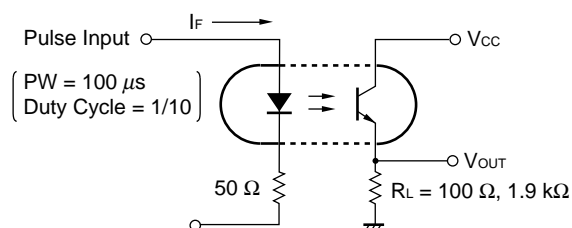
<sup>\*1</sup> PW = 100 μs, Duty Cycle = 1%

<sup>\*2</sup> AC voltage for 1 minute at T<sub>A</sub> = 25°C, RH = 60% between input and output

**ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C)**

Parameter		Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Diode	Forward Voltage	V <sub>F</sub>	I <sub>F</sub> = 5 mA		1.1	1.3	V
	Reverse Current	I <sub>R</sub>	V <sub>R</sub> = 5 V			5	μA
	Terminal Capacitance	C <sub>t</sub>	V = 0 V, f = 1.0 MHz		30		pF
Transistor	Collector to Emitter Dark Current	I <sub>CEO</sub>	V <sub>CE</sub> = 120 V, I <sub>F</sub> = 0 mA			100	nA
Coupled	Current Transfer Ratio (I <sub>C</sub> /I <sub>F</sub> )	CTR1	I <sub>F</sub> = 1 mA, V <sub>CE</sub> = 5 V	25	75	100	%
		CTR2	I <sub>F</sub> = 5 mA, V <sub>CE</sub> = 5 V	50	125	200	%
	Collector Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>F</sub> = 10 mA, I <sub>C</sub> = 2 mA			0.3	V
	Isolation Resistance	R <sub>I-O</sub>	V <sub>I-O</sub> = 1.0 kV <sub>DC</sub>	10 <sup>11</sup>			Ω
	Isolation Capacitance	C <sub>I-O</sub>	V = 0 V, f = 1.0 MHz		0.5		pF
	Rise Time <sup>*1</sup>	t <sub>r</sub>	V <sub>CC</sub> = 5 V, I <sub>C</sub> = 2 mA, R <sub>L</sub> = 100 Ω		3		μs
	Fall Time <sup>*1</sup>	t <sub>f</sub>			4		
	Turn-on Time <sup>*1</sup>	t <sub>on</sub>	V <sub>CC</sub> = 5 V, I <sub>F</sub> = 5 mA, R <sub>L</sub> = 1.9 kΩ		5	60	μs
	Turn-off Time <sup>*1</sup>	t <sub>off</sub>			25	60	

**\*1** Test circuit for switching time

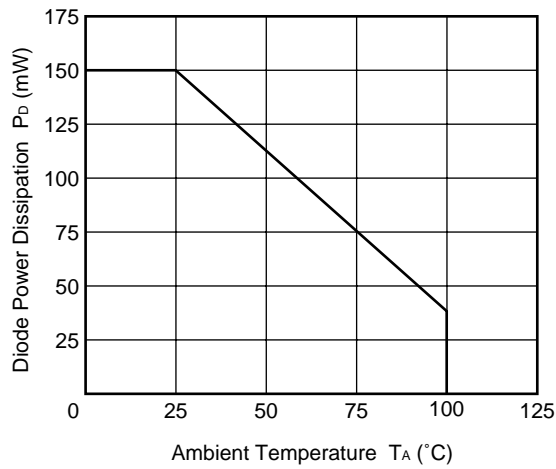


**CAUTIONS REGARDING NOISE**

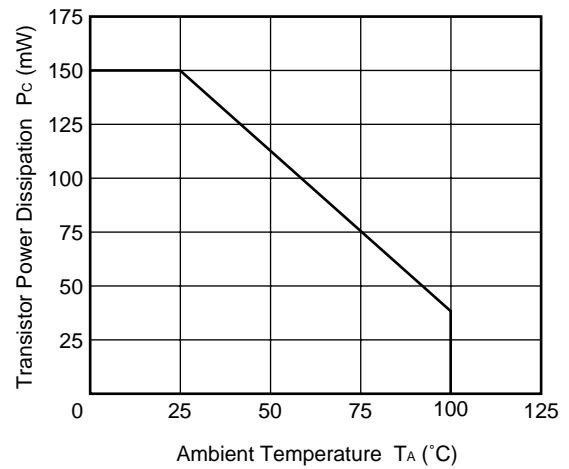
Be aware that when voltage is applied suddenly between the photocoupler's input and output or between corrector-emitters at startup, the output side may enter the on state, even if the voltage is within the absolute maximum ratings.

**TYPICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ , unless otherwise specified)**

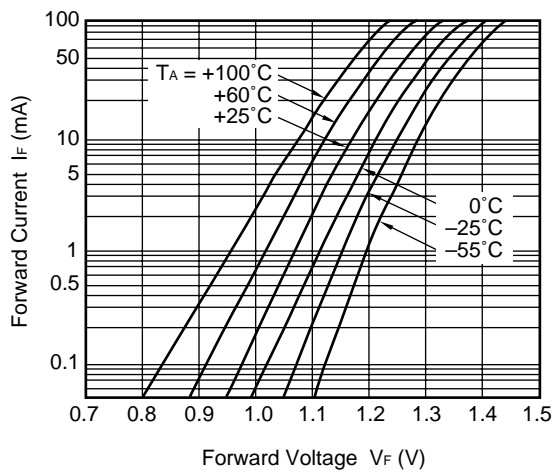
**DIODE POWER DISSIPATION vs. AMBIENT TEMPERATURE**



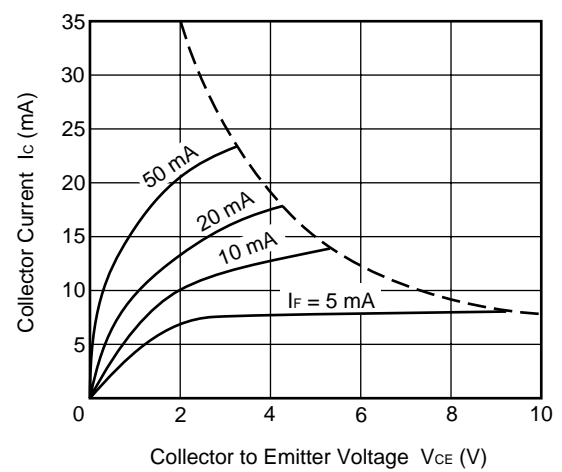
**TRANSISTOR POWER DISSIPATION vs. AMBIENT TEMPERATURE**



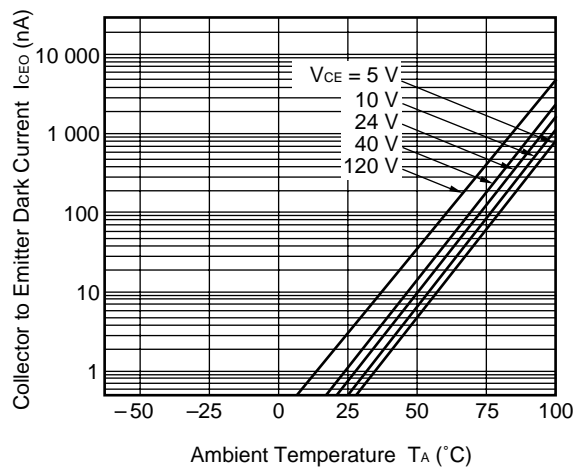
**FORWARD CURRENT vs. FORWARD VOLTAGE**



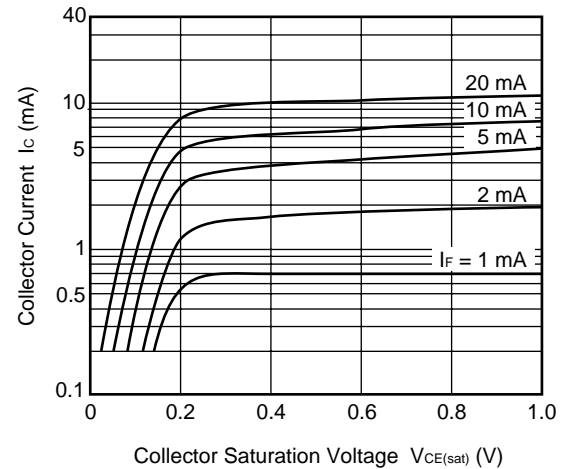
**COLLECTOR CURRENT vs. COLLECTOR TO EMITTER VOLTAGE**



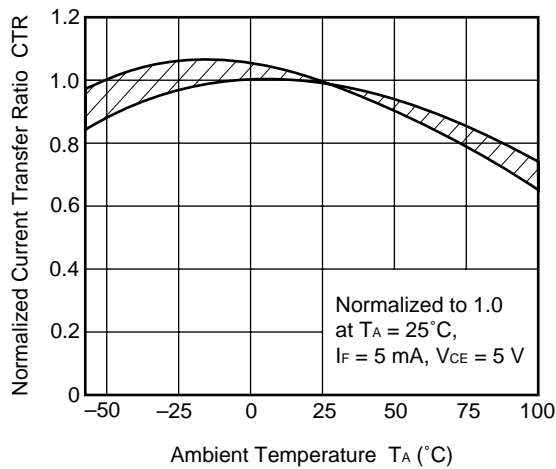
**COLLECTOR TO EMITTER DARK CURRENT vs. AMBIENT TEMPERATURE**



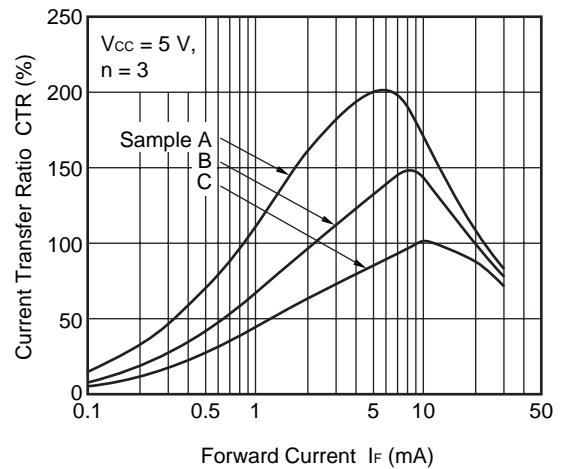
**COLLECTOR CURRENT vs. COLLECTOR SATURATION VOLTAGE**



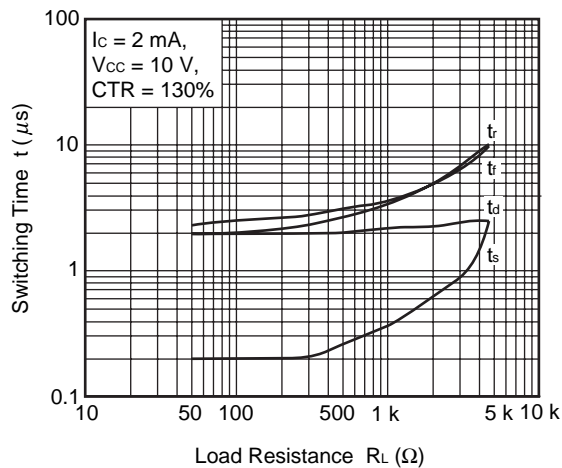
NORMALIZED CURRENT TRANSFER RATIO vs. AMBIENT TEMPERATURE



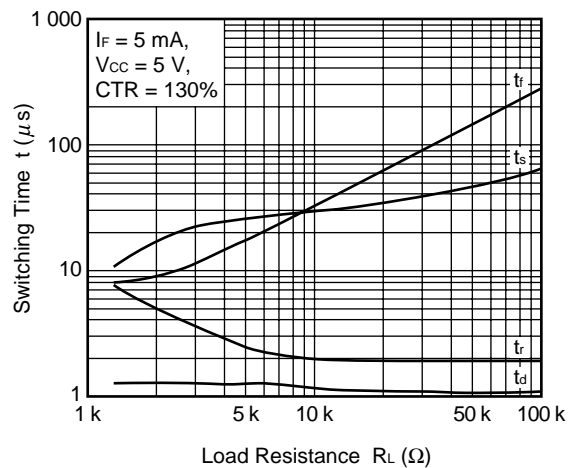
CURRENT TRANSFER RATIO vs. FORWARD CURRENT



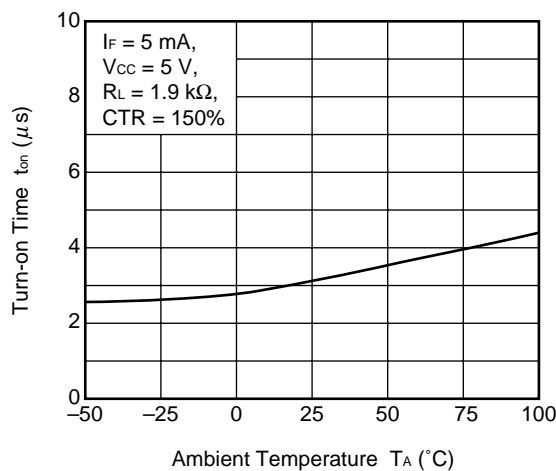
SWITCHING TIME vs. LOAD RESISTANCE



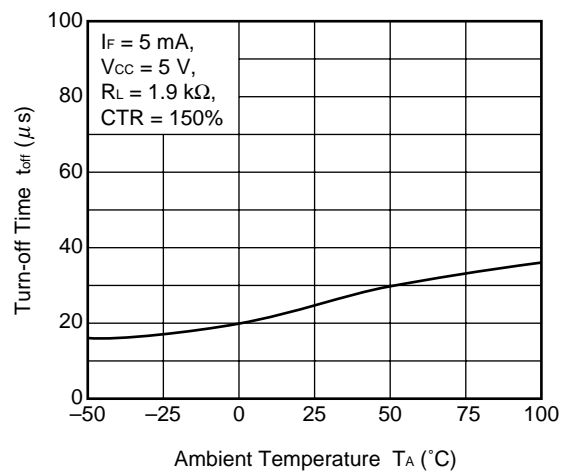
SWITCHING TIME vs. LOAD RESISTANCE

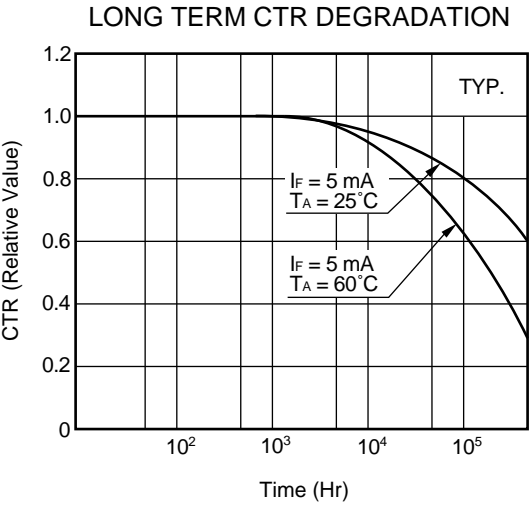


TURN-ON TIME vs. AMBIENT TEMPERATURE



TURN-OFF TIME vs. AMBIENT TEMPERATURE



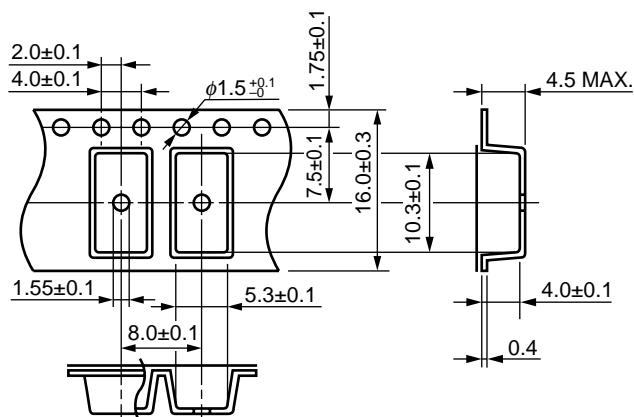


**Remark** The graphs indicate nominal characteristics.



### ★ TAPING SPECIFICATIONS (UNIT: mm)

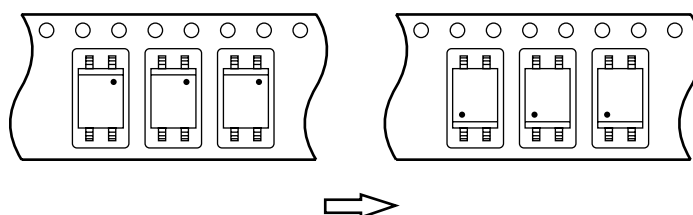
### Outline and Dimensions (Tape)



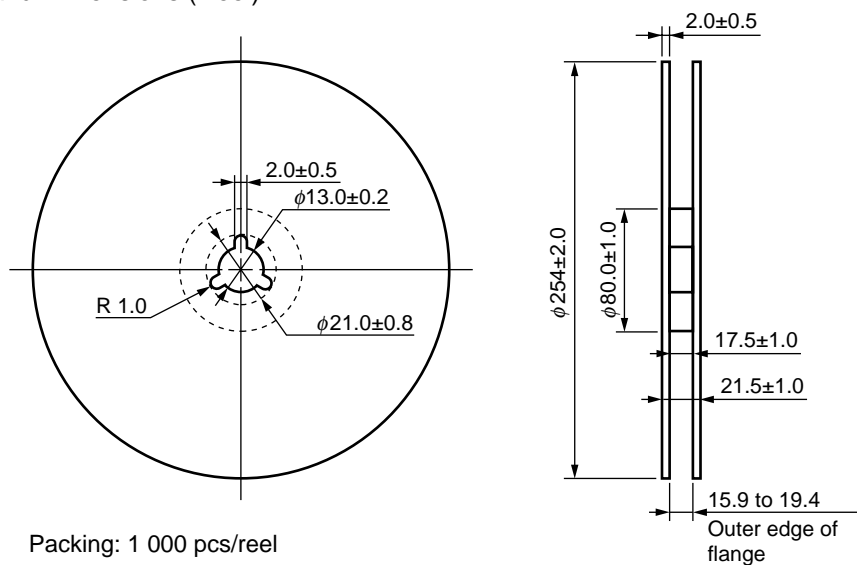
Tape Direction

PS2513L-1-E3

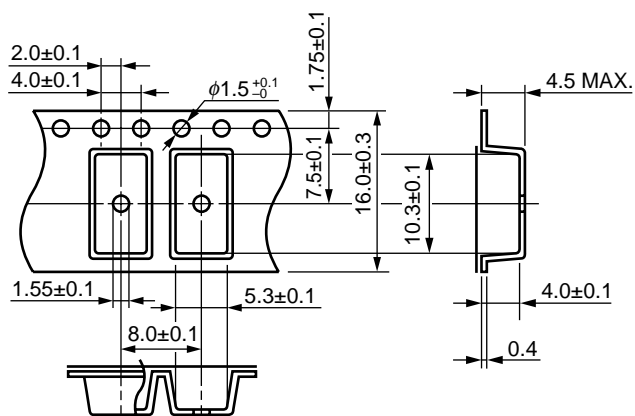
PS2513L-1-E4



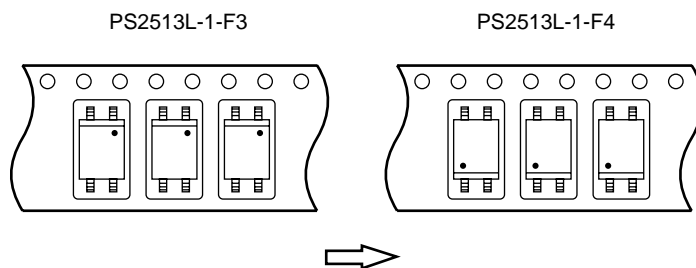
### Outline and Dimensions (Reel)



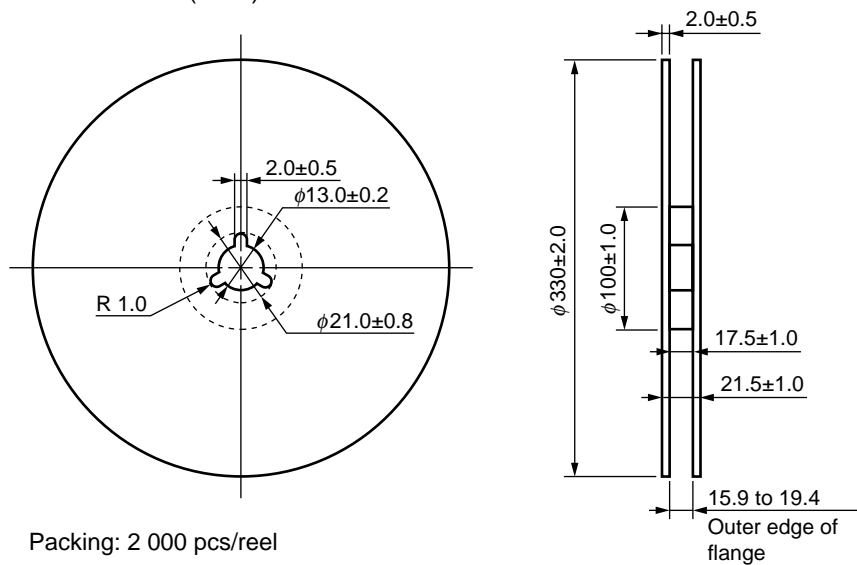
Outline and Dimensions (Tape)



Tape Direction



Outline and Dimensions (Reel)

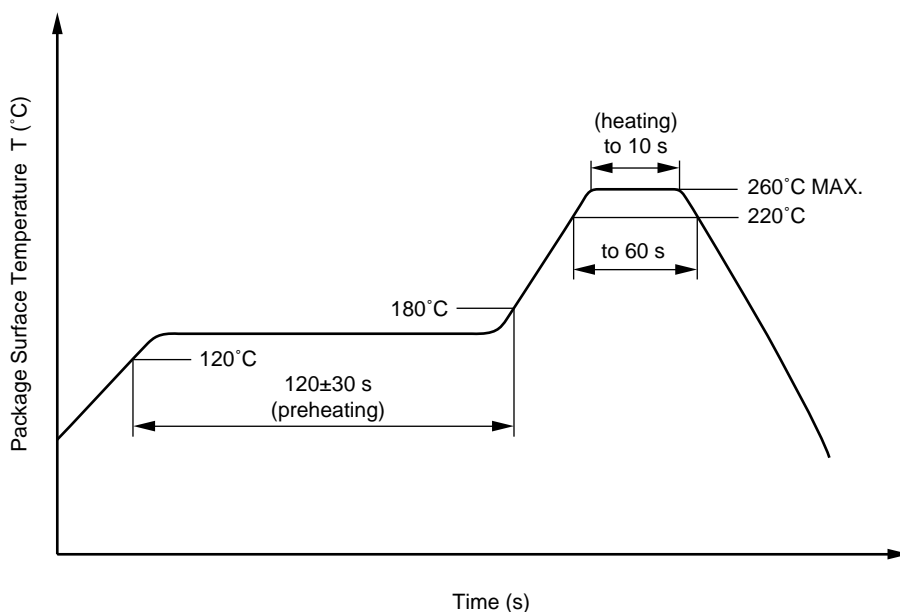


## RECOMMENDED SOLDERING CONDITIONS

### (1) Infrared reflow soldering

- Peak reflow temperature 260°C or below (package surface temperature)
- Time of peak reflow temperature 10 seconds or less
- Time of temperature higher than 220°C 60 seconds or less
- Time to preheat temperature from 120 to 180°C 120±30 s
- Number of reflows Three
- Flux Rosin flux containing small amount of chlorine (The flux with a maximum chlorine content of 0.2 Wt% is recommended.)

Recommended Temperature Profile of Infrared Reflow



### (2) Wave soldering

- Temperature 260°C or below (molten solder temperature)
- Time 10 seconds or less
- Preheating conditions 120°C or below (package surface temperature)
- Number of times One (Allowed to be dipped in solder including plastic mold portion.)
- Flux Rosin flux containing small amount of chlorine (The flux with a maximum chlorine content of 0.2 Wt% is recommended.)

### (3) Cautions

- Fluxes  
Avoid removing the residual flux with freon-based and chlorine-based cleaning solvent.

## USAGE CAUTIONS

1. Protect against static electricity when handling.
2. Avoid storage at a high temperature and high humidity.

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M8E 00.4-0110

**SAFETY INFORMATION ON THIS PRODUCT**

<div data-bbox="177 271 288 311" data-label="Section-Header"> <p><b>Caution</b></p> </div> <p>GaAs Products</p>	<p>The product contains gallium arsenide, GaAs. GaAs vapor and powder are hazardous to human health if inhaled or ingested.</p> <ul style="list-style-type: none"> <li>• Do not destroy or burn the product.</li> <li>• Do not cut or cleave off any part of the product.</li> <li>• Do not crush or chemically dissolve the product.</li> <li>• Do not put the product in the mouth.</li> </ul> <p>Follow related laws and ordinances for disposal. The product should be excluded from general industrial waste or household garbage.</p>
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► For further information, please contact

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